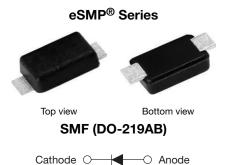
Vishay Semiconductors

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Hyperfast Rectifier, 2 A FRED Pt®



LINKS TO ADDITIONAL RESOURCES



PRIMARY CHARACTERISTICS				
I _{F(AV)}	2 A			
V _R	200 V			
V _F at I _F (typ. 125 °C)	0.75 V			
t _{rr}	25 ns			
T _J max.	175 °C			
Package	SMF (DO-219AB)			
Circuit configuration	Single			

FEATURES

- Hyperfast recovery time, reduced Q_{rr}, and soft recovery
- 175 °C maximum operating junction temperature
- Specified for output and snubber operation
- Low forward voltage drop
- · Low leakage current
- Meets MSL level 1, per J-STD-020, LF maximum peak of 260 °C
- Wave and reflow solderable
- Compatible to SOD-123W package case outline
- AEC-Q101 qualified, meets JESD 201 class 2 whisker test
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

DESCRIPTION / APPLICATIONS

State of the art hyperfast recovery rectifiers designed with optimized performance of forward voltage drop and hyperfast recovery.

The planar structure and the platinum doped life time control guarantee the best overall performance, ruggedness, and reliability characteristics.

These devices are intended for use in snubber boost, lighting, piezo-injection, as high frequency rectifiers, and freewheeling diodes.

Their extremely optimized stored charge and low recovery current minimize the switching losses and reduce power dissipation in the switching element.

MECHANICAL DATA

Case: SMF (DO-219AB)

Molding compound meets UL 94 V-0 flammability rating Halogen-free, RoHS-compliant

Terminals: matte tin plated leads, solderable per J-STD-002

Polarity: color band denotes cathode end

ABSOLUTE MAXIMUM RATINGS						
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS		
Peak repetitive reverse voltage	V _{RRM}		200	V		
Average rectified forward current	I _{F(AV)}	$T_{\rm C} = 150 \ ^{\circ}{\rm C} \ ^{(1)}$	2	^		
Non-repetitive peak surge current	I _{FSM}	T _J = 25 °C	50	A		
Operating junction and storage temperature range	T _J , T _{Stg}		-65 to +175	°C		

Note

 $^{(1)}\,$ Device on PCB with 8 mm x 16 mm soldering lands

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(Pb) RoHS

COMPLIANT



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ELECTRICAL SPECIFICATIONS ($T_J = 25 \text{ °C}$ unless otherwise specified)						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Breakdown voltage, blocking voltage	V_{BR} , V_{R}	I _R = 100 μA	200	-	-	
Forward voltage	V	I _F = 2 A	-	0.88	0.95	V
	V _F	I _F = 2 A, T _J = 125 °C	-	0.75	0.82	
Reverse leakage current	1	V _R = V _R rated	-	-	2	
neverse leakage current	I _R	$T_J = 125 \text{ °C}, V_R = V_R \text{ rated}$	-	1	8	μA
Junction capacitance	CT	V _R = 200 V	-	8	-	pF

DYNAMIC RECOVERY CHARACTERISTICS ($T_J = 25 \text{ °C}$ unless otherwise specified)							
PARAMETER	SYMBOL	TEST CO	MIN.	TYP.	MAX.	UNITS	
		I _F = 1 A, dI _F /dt = 50 A	õs, V _R = 30 V	-	24	-	
Reverse recovery time	+	$I_F = 0.5 \text{ A}, I_R = 1 \text{ A}, I_{rr}$	= 0.25 A	-	-	25	ns
Reverse recovery time	t _{rr}	T _J = 25 °C		-	16	-	
		T _J = 125 °C		-	22	-	
Dook rocovery ourrent	1	T _J = 25 °C	I _F = 2 A dI _F /dt = 200 A/μs V _B = 160 V	-	2	-	А
Peak recovery current I _{RRM}	IRRM	T _J = 125 °C		-	3	-	A
	0	T _J = 25 °C		-	16	-	nC
Reverse recovery charge	Q _{rr}	T _J = 125 °C		-	30	-	ne

THERMAL - MECHANICAL SPECIFICATIONS						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Maximum junction and storage temperature range	T _J , T _{Stg}		-65	-	175	°C
Thermal resistance, junction to mount	R _{thJM}	Device mounted on PCB with 8 mm x 16 mm soldering lands	-	-	15	°C/W
Thermal resistance, junction to ambient	R _{thJA}	Device mounted on PCB with 2 mm x 3.5 mm soldering lands	-	-	130	°C/W
Approvimeto weight				0.015		g
Approximate weight				0.0005		oz.
Marking device		Case style SMF (DO-219AB)		М	EH	



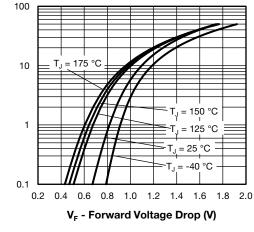
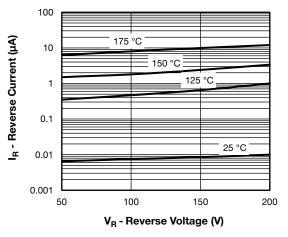
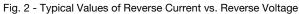


Fig. 1 - Typical Forward Voltage Drop Characteristics



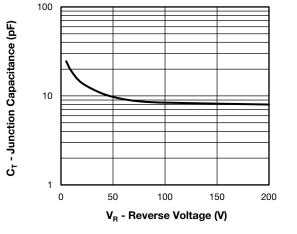


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Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

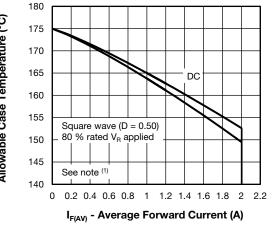


Fig. 4 - Maximum Allowable Case Temperature vs. Average Forward Current

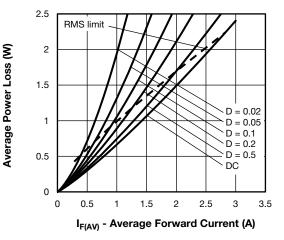


Fig. 5 - Forward Power Loss Characteristics

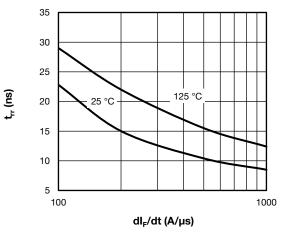
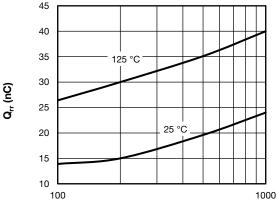


Fig. 6 - Typical Reverse Recovery Time vs. dl_F/dt



dl_F/dt (A/µs)

Fig. 7 - Typical Stored Charge vs. dl_F/dt

Note

⁽¹⁾ Formula used: $T_C = T_J - (Pd + Pd_{REV}) \times R_{thJC}$;

 $Pd = forward power loss = I_{F(AV)} \times V_{FM} at (I_{F(AV)}/D)$ (see fig. 5); Pd_{REV} = inverse power loss = $V_{R1} \times I_R (1 - D)$; I_R at V_{R1} = rated V_R

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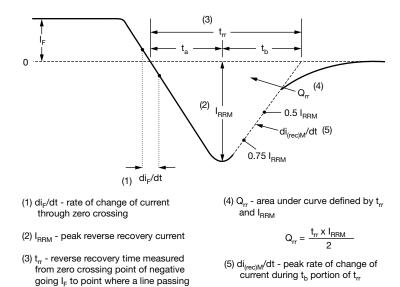
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Allowable Case Temperature (°C)

VS-2EFH02HM3

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extrapolated to zero current. Fig. 8 - Reverse Recovery Waveform and Definitions

through 0.75 I_{RBM} and 0.50 I_{RBM}

ORDERING INFORMATION TABLE

SHAY

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Device code	VS-	2	Е	F	н	02	н	М3
	1	2	3	4	5	6	7	8
	2	- Cur - Circ	rrent rat	nicondu ing (2 = figuratic diode	2 A)	oduct		
	4 · 5 ·		SMF pa cess ty	•				
	6 · 7 ·	- Vol - H =	tage co AEC-C	ast recor de (02 = 101 qua jen-free	200 V) alified	complia	ant, and	termin

ORDERING INFORMATION (Example)							
PREFERRED P/N	QUANTITY PER REEL	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION				
VS-2EFH02HM3/I	10 000	10 000	13" diameter plastic tape and reel				

LINKS TO RELATED DOCUMENTS				
Dimensions	www.vishay.com/doc?95572			
Part marking information	www.vishay.com/doc?95618			
Packaging information	www.vishay.com/doc?95577			
SPICE model	www.vishay.com/doc?96013			

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Document Number: 95790

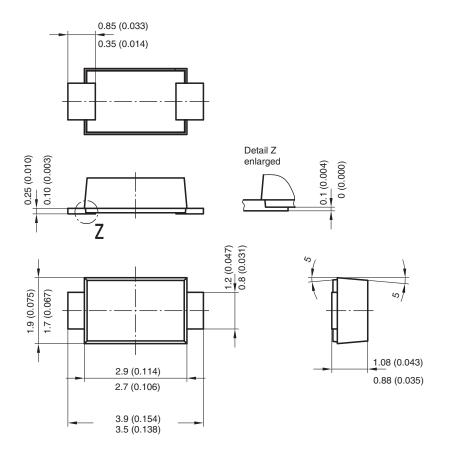
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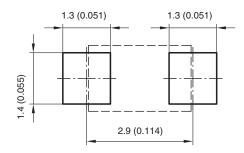
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SMF (DO-219AB)

DIMENSIONS in millimeters (inches)



Foot print recommendation:



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